CY62157H MoBL®

8-Mbit (512K words × 16 bit) Static RAM with Error Correcting Code (ECC)

Features

- Ultra-low standby current
  - Typical standby current: 5.5 μA
  - Maximum standby current: 16 μA
- High speed: 45 ns
- Voltage range: 2.2 V to 3.6 V
- Embedded Error Correcting Code (ECC) for single-bit error correction
- 1.0 V data retention
- Transistor-transistor logic (TTL) compatible inputs and outputs
- Available in Pb-free 48-ball VFBGA and 48-pin TSOP I packages

Functional Description

CY62157H is a high-performance CMOS low-power (MoBL) SRAM device with Embedded Error Correcting Code. ECC logic can detect and correct single bit error in accessed location.

This device is offered in dual chip enable option. Dual chip enable devices are accessed by asserting both chip enable inputs – $\overline{CE}_1$ as LOW and CE_2 as HIGH.

Data writes are performed by asserting the Write Enable input ($\overline{WE}$ LOW), and providing the data and address on device data (I/O_0 through I/O_{15}) and address (A_0 through A_{18}) pins respectively. The Byte High/Low Enable ($\overline{BHE}$, $\overline{BLE}$) inputs control byte writes, and write data on the corresponding I/O lines to the memory location specified. $\overline{BHE}$ controls I/O_8 through I/O_{15} and $\overline{BLE}$ controls I/O_0 through I/O_7.

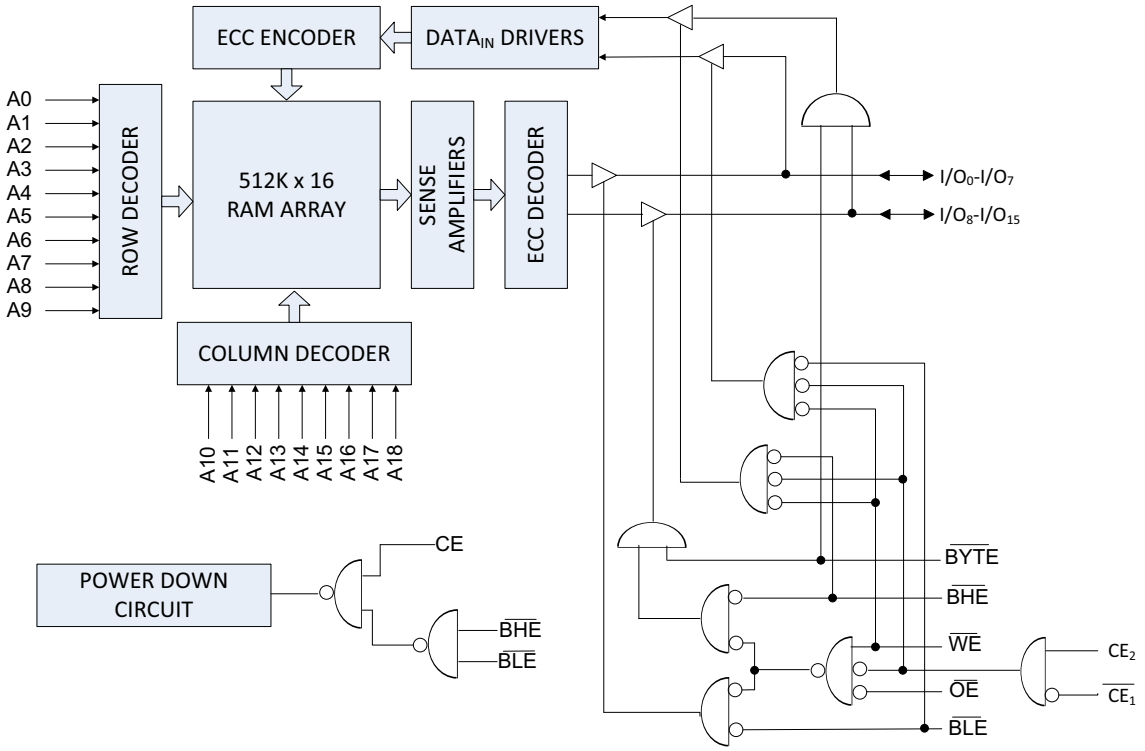
Data reads are performed by asserting the Output Enable ($\overline{OE}$) input and providing the required address on the address lines. Read data is accessible on I/O lines (I/O_0 through I/O_{15}). Byte accesses can be performed by asserting the required byte enable signal ($\overline{BHE}$, $\overline{BLE}$) to read either the upper byte or the lower byte of data from the specified address location.

All I/Os (I/O_0 through I/O_{15}) are placed in a high impedance state when the device is deselected ($\overline{CE}_1$ HIGH / CE_2 LOW for dual chip enable device), or control signals are de-asserted ($\overline{OE}$, $\overline{BLE}$, $\overline{BHE}$).

These devices also have a unique “Byte Power down” feature, where, if both the Byte Enables ($\overline{BHE}$ and $\overline{BLE}$) are disabled, the devices seamlessly switch to standby mode irrespective of the state of the chip enable(s), thereby saving power.

The CY62157H device is available in a Pb-free 48-ball VFBGA and 48-pin TSOP I packages. The logic block diagram is on page 2.

Logic Block Diagram



Contents

Pin Configurations **4**
Product Portfolio **5**
Maximum Ratings **6**
Operating Range **6**
DC Electrical Characteristics **6**
Capacitance **7**
Thermal Resistance **7**
AC Test Loads and Waveforms **7**
Data Retention Characteristics **8**
Data Retention Waveform **8**
Switching Characteristics **9**
Switching Waveforms **10**
Truth Table – CY62157H **15**
Ordering Information **16**
Ordering Code Definitions 16
Package Diagrams **17**
Acronyms **19**
Document Conventions **19**
Units of Measure 19
Document History Page **20**
Sales, Solutions, and Legal Information **21**
Worldwide Sales and Design Support 21
Products 21
PSoC®Solutions 21
Cypress Developer Community 21
Technical Support 21

Pin Configurations

Figure 1. 48-ball VFBGA (6 × 8 × 1mm) pinout [1]

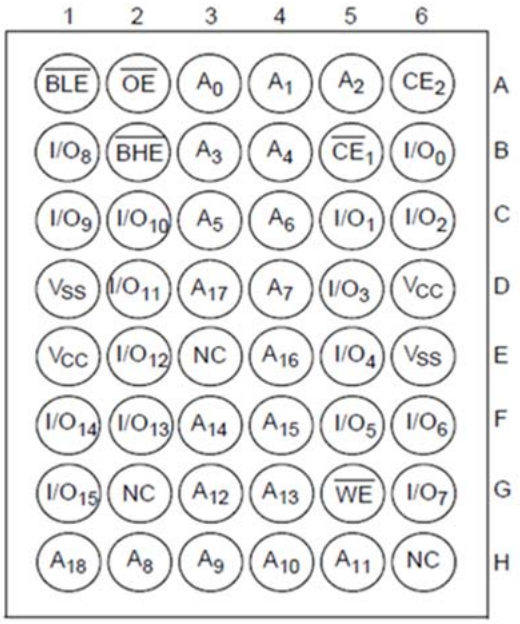
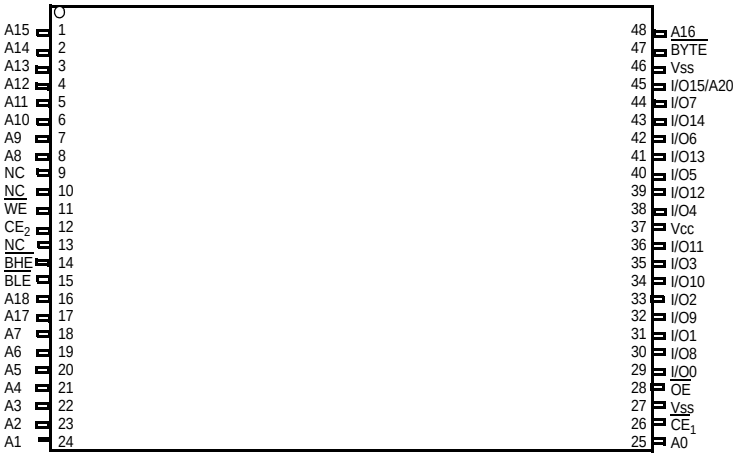


Figure 2. 48-pin TSOP I pinout (Dual Chip Enable) [1, 2]



Notes

1. NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.
2. Tie the BYTE pin in the 48-pin TSOP I package to V_{CC} to use the device as a 1 M × 16 SRAM. The 48-pin TSOP I package can also be used as a 2 M × 8 SRAM by tying the BYTE signal to V_{SS}. In the 2 M × 8 configuration, Pin 45 is the extra address line A20, while BHE, BLE, and I/O_8 to I/O_{14} pins are not used and can be left floating.

Product Portfolio

Product	Features and Options (see the Pin Configurations section)	Range	V_{CC} Range (V)	Speed (ns)	Power Dissipation			
					Operating I_{CC}, (mA) f = f_{max}		Standby, I_{SB2} (µA)	
					Typ [3]	Max	Typ [3]	Max
CY62157H30	Dual Chip Enable	Industrial	2.2 V–3.6 V	45	29	36	5.5	16

Note
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V (for V_{CC} range of 2.2 V–3.6 V), T_A = 25 °C.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... –65 °C to + 150 °C

Ambient temperature with power applied ..... –55 °C to + 125 °C

Supply voltage to ground potential ..... –0.2 V to V_{CC} + 0.3 V

DC voltage applied to outputs in High Z state [4] ..... –0.2 V to V_{CC} + 0.3 V

DC input voltage [4] ..... –0.2 V to V_{CC} + 0.3 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... >2001 V

Latch up current ..... >140 mA

Operating Range

Grade	Ambient Temperature	V_{CC}
Industrial	–40 °C to +85 °C	2.2 V to 3.6 V

DC Electrical Characteristics

Over the Operating Range of –40 °C to 85 °C

Parameter	Description		Test Conditions		45 ns			Unit
					Min	Typ [5]	Max	
V_{OH}	Output HIGH voltage	2.2 V to 2.7 V	V_{CC} = Min, I_{OH} = –0.1 mA		2	–	–	V
		2.7 V to 3.6 V	V_{CC} = Min, I_{OH} = –1.0 mA		2.4	–	–	
V_{OL}	Output LOW voltage	2.2 V to 2.7 V	V_{CC} = Min, I_{OL} = 0.1 mA		–	–	0.4	V
		2.7 V to 3.6 V	V_{CC} = Min, I_{OL} = 2.1 mA		–	–	0.4	
V_{IH}	Input HIGH voltage	2.2 V to 2.7 V	–		1.8	–	V_{CC} + 0.3	V
		2.7 V to 3.6 V	–		2	–	V_{CC} + 0.3	
V_{IL}	Input LOW voltage [4]	2.2 V to 2.7 V	–		–0.3	–	0.6	V
		2.7 V to 3.6 V	–		–0.3	–	0.8	
I_{IX}	Input leakage current		GND ≤ V_{IN} ≤ V_{CC}		–1	–	+1	µA
I_{OZ}	Output leakage current		GND ≤ V_{OUT} ≤ V_{CC}, Output disabled		–1	–	+1	µA
I_{CC}	V_{CC} operating supply current		V_{CC} = Max, I_{OUT} = 0 mA, CMOS levels	f = f_{MAX}	–	29.0	36.0	mA
				f = 1 MHz	–	7.0	9.0	mA
I_{SB1} [6]	Automatic power down current – CMOS inputs; V_{CC} = 2.2 to 3.6 V		$\overline{CE_1}$ ≥ V_{CC} – 0.2 V or CE_2 ≤ 0.2 V, ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V, V_{IN} ≤ 0.2 V, f = f_{max} (address and data only), f = 0 ($\overline{OE}$, and $\overline{WE}$), V_{CC} = $V_{CC(max)}$		–	5.5	16.0	µA
I_{SB2} [6]	Automatic power down current – CMOS inputs V_{CC} = 2.2 to 3.6 V		$\overline{CE_1}$ ≥ V_{CC} – 0.2 V or CE_2 ≤ 0.2 V, ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V, f = 0, V_{CC} = $V_{CC(max)}$	25 °C [7]	–	5.5	6.5	µA
				40 °C [7]	–	6.3	8.0	
				85 °C	–	12.0[7]	16.0	

Notes

4. $V_{IL(min)}$ = –2.0 V and $V_{IH(max)}$ = V_{CC} + 2 V for pulse durations of less than 20 ns.
5. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V (for V_{CC} range of 2.2 V–3.6 V), T_A = 25 °C.
6. Chip enables ($\overline{CE_1}$ and CE_2) must be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
7. The I_{SB2} limits at 25 °C, 70 °C, 40 °C and typical limit at 85 °C are guaranteed by design and not 100% tested.

Capacitance

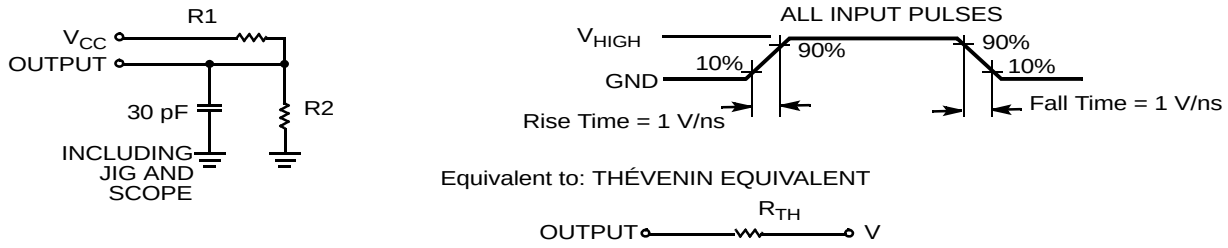
Parameter [8]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [8]	Description	Test Conditions	48-pin TSOP I	48-ball VFBGA	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	57.99	31.50	°C/W
Θ_{JC}	Thermal resistance (junction to case)		13.42	15.75	°C/W

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms



Parameters	2.5 V	3.0 V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Note
8. Tested initially and after any design or process changes that may affect these parameters.

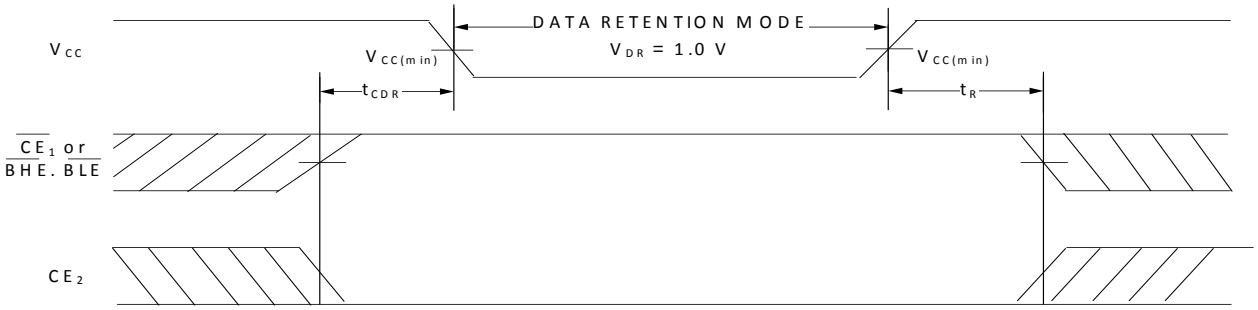
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ [9]	Max	Unit
V_{DR}	V_{CC} for data retention		1	–	–	V
I_{CCDR}[10, 11]	Data retention current	2.2 V < V_{CC} ≤ 3.6 V, $\overline{CE}_1 \geq V_{CC} - 0.2$ V or $CE_2 \leq 0.2$ V, ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	–	5.5	16.0	µA
t_{CDR}[12]	Chip deselect to data retention time		0	–	–	–
t_R[13]	Operation recovery time		45	–	–	ns

Data Retention Waveform

Figure 4. Data Retention Waveform [14]



Notes
9. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V (for V_{CC} range of 2.2 V–3.6 V), T_A = 25 °C.
10. Chip enables ($\overline{CE}_1$ and CE_2) must be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
11. I_{CCDR} is guaranteed only after the device is firs powered up to V_{CC}(min) and then brought down to V_{DR}.
12. Tested initially and after any design or process changes that may affect these parameters.
13. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)}$ ≥ 100 µs or stable at $V_{CC(min)}$ ≥ 100 µs.
14. $\overline{BHE}$.$\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Deselect the chip by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

Switching Characteristics

Parameter [15]	Description	45 ns		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to data valid	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[16]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[16, 17]	–	18	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Low-Z[16]	10	–	ns
t_{HZCE}	$\overline{CE}_1$ HIGH and CE_2 LOW to High-Z[16, 17]	–	18	ns
t_{PU}	$\overline{CE}_1$ LOW and CE_2 HIGH to power-up	0	–	ns
t_{PD}	$\overline{CE}_1$ HIGH and CE_2 LOW to power-down	–	45	ns
t_{DBE}	BLE / BHE LOW to data valid	–	45	ns
t_{LZBE}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Low-Z[16]	5	–	ns
t_{HZBE}	$\overline{BLE}$ / $\overline{BHE}$ HIGH to High-Z[16, 17]	–	18	ns
Write Cycle [18, 19]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{BW}	$\overline{BLE}$ / $\overline{BHE}$ LOW to write end	35	–	ns
t_{SD}	Data setup to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[16, 17]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[16]	10	–	ns

Notes

15. Test conditions assume signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for $V_{CC} \geq 3$ V) and $V_{CC}/2$ (for $V_{CC} < 3$ V), and input pulse levels of 0 to 3 V (for $V_{CC} \geq 3$ V) and 0 to V_{CC} (for $V_{CC} < 3$V). Test conditions for the read cycle use output loading shown in AC Test Loads and Waveforms section, unless specified otherwise.
16. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
17. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
18. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
19. The minimum write cycle pulse width for Write Cycle No. 1 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

Figure 5. Read Cycle No. 1 of CY62157H (Address Transition Controlled) [20, 21]

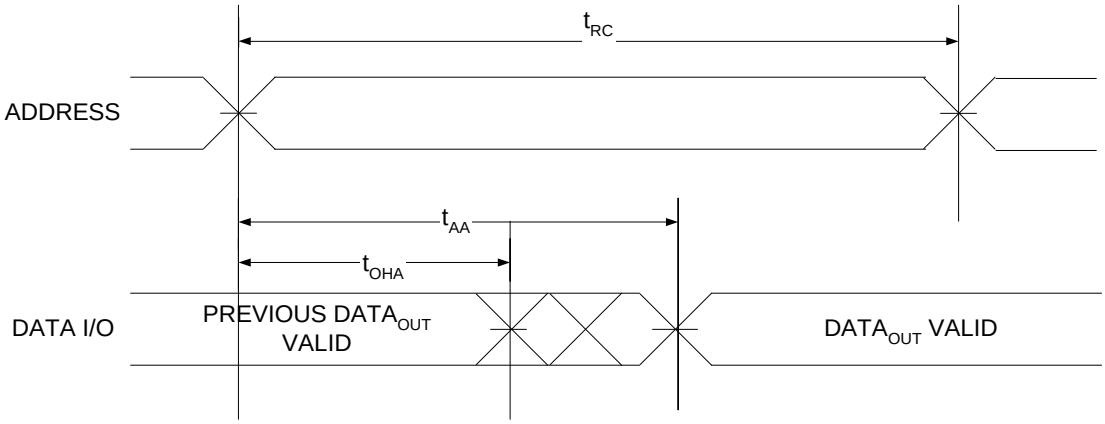
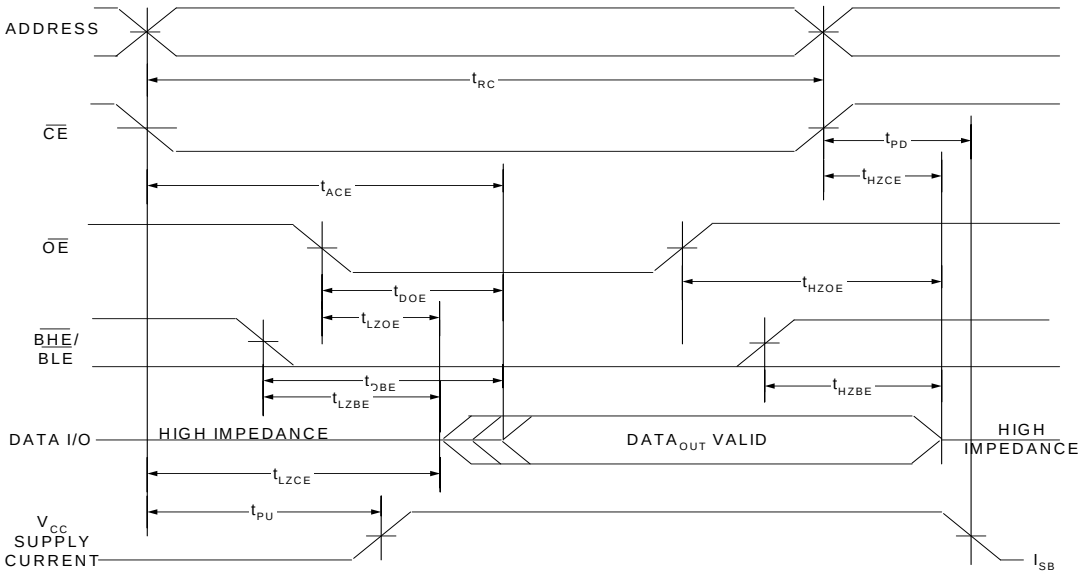


Figure 6. Read Cycle No. 2 ($\overline{OE}$ Controlled) [21, 22, 23]

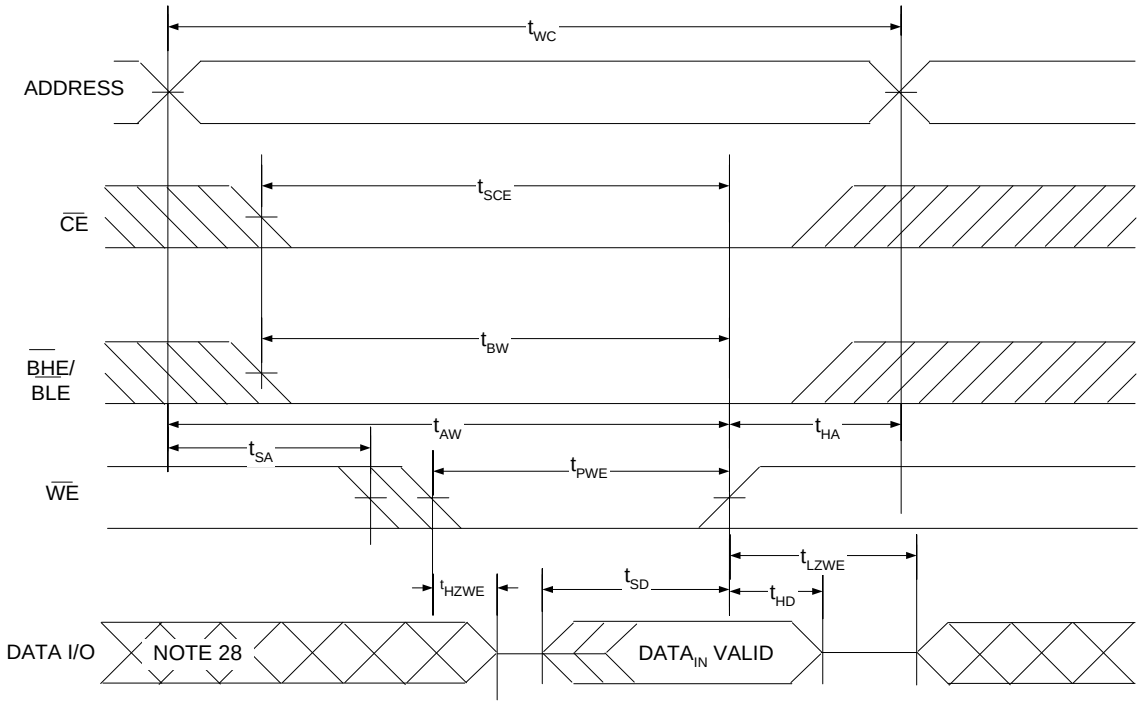


Notes

20. The device is continuously selected. $\overline{OE}$ = V_{IL}, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}.
21. $\overline{WE}$ is HIGH for read cycle.
22. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
23. Address valid prior to or coincident with $\overline{CE}$ LOW transition.

Switching Waveforms (continued)

Figure 7. Write Cycle No. 1 (WE Controlled, OE LOW) [24, 25, 26, 27]

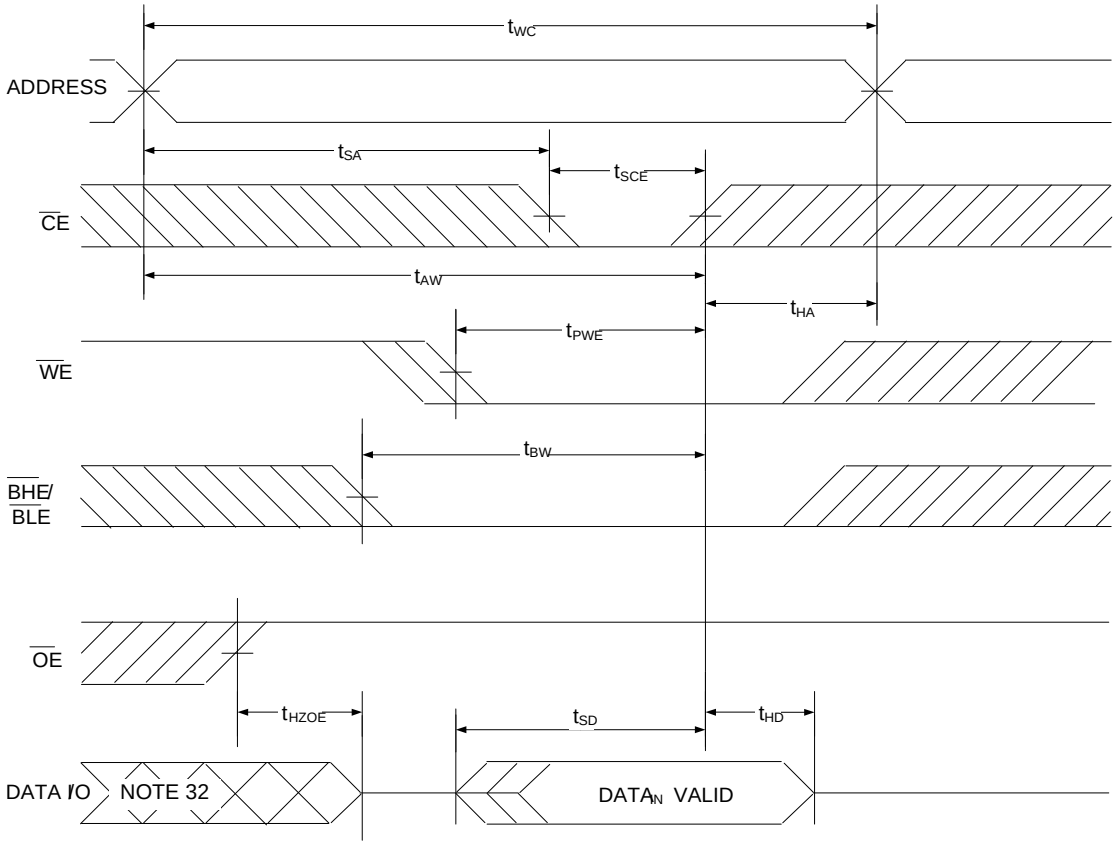


Notes

24. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
25. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
26. Data I/O is in high impedance state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.
27. The minimum write cycle pulse width for Write Cycle No. 1 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{HZWE} and t_{SD}.
28. During this period the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 2 ($\overline{CE}$ Controlled) [29, 30, 31]

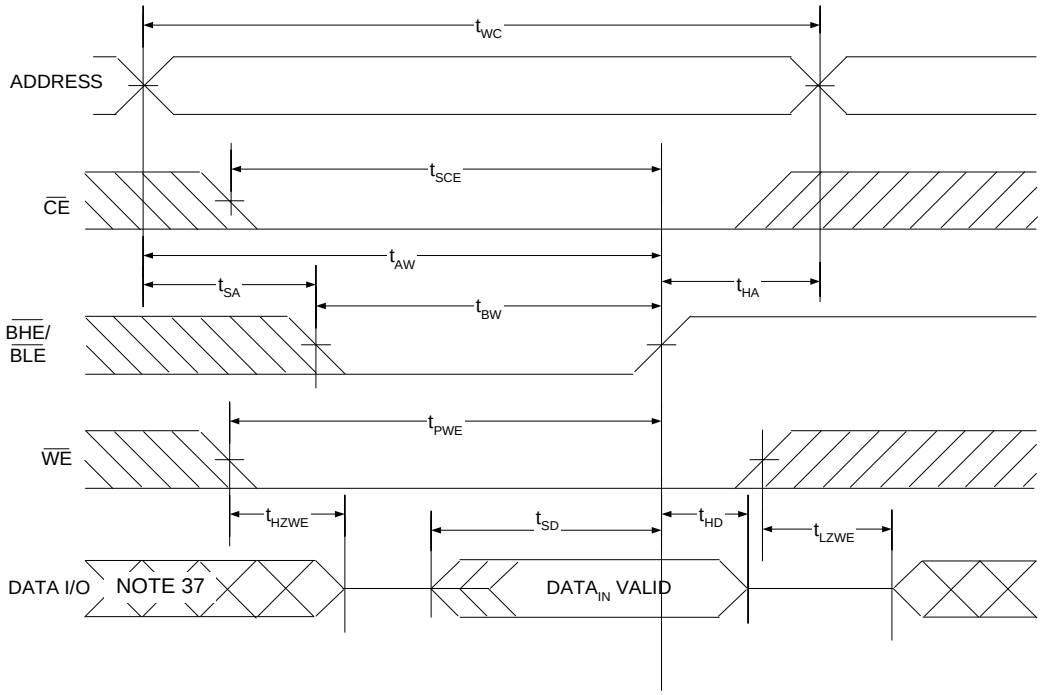


Notes

29. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
30. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
31. Data I/O is in high impedance state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.
32. During this period the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 9. Write Cycle No. 3 (BHE/BLE controlled, OE LOW) [33, 34, 35, 36]

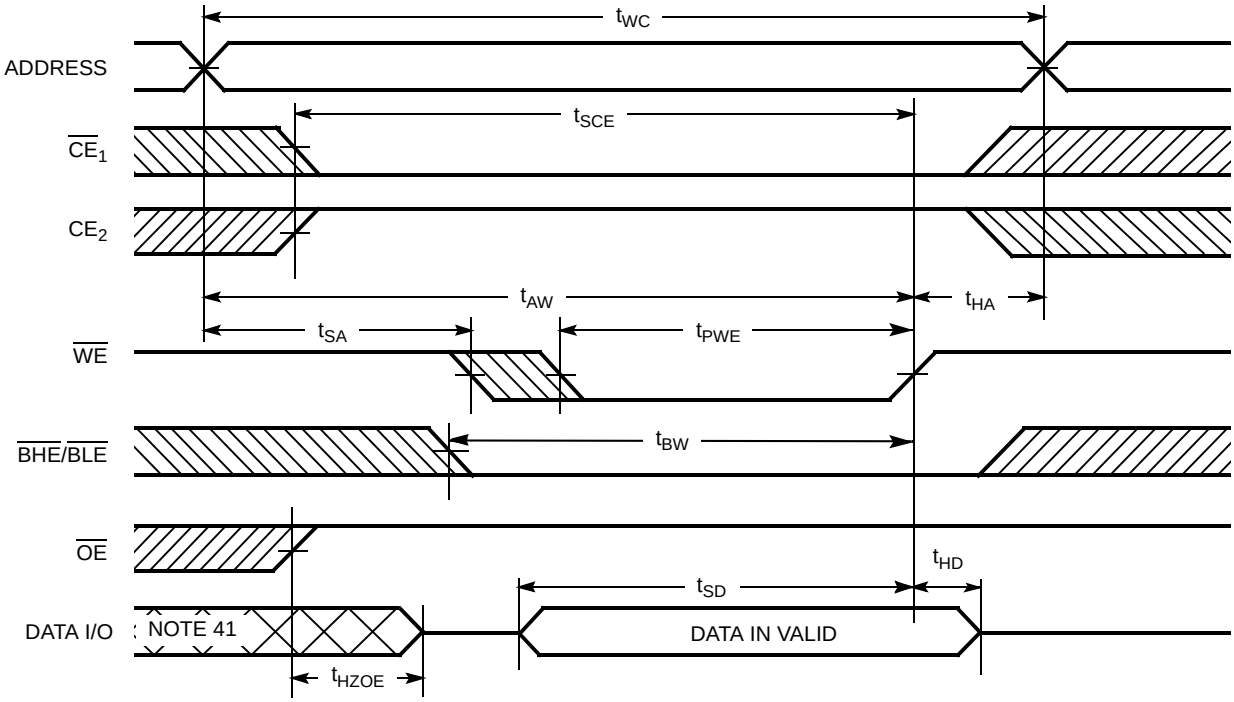


Notes

33. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE_1}$ and CE_2. When $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE_1}$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
34. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE_1}$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
35. Data I/O is in high impedance state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.
36. The minimum write cycle pulse width for Write Cycle No. 3 ($\overline{BHE}$/$\overline{BLE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{HZWE} and t_{SD}.
37. During this period the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 10. Write Cycle No. 4 ($\overline{WE}$ Controlled) [38, 39, 40]



Notes

38. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE_1}$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
39. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
40. If $\overline{CE_1}$ goes HIGH and CE_2 goes LOW simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
41. During this period the I/Os are in output state. Do not apply input signals.

Truth Table – CY62157H

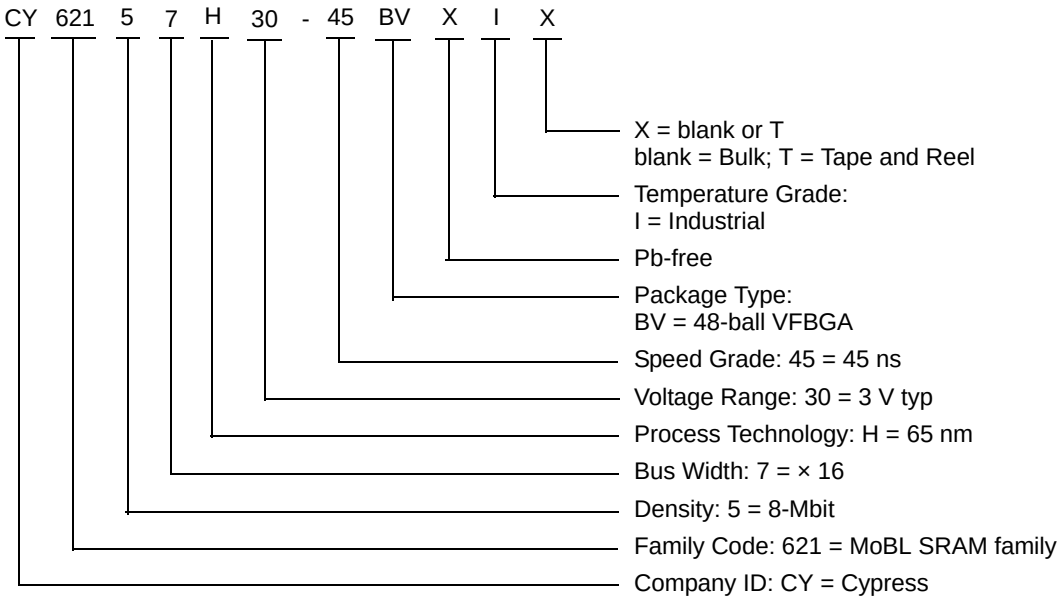
$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X[42]	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
X[42]	L	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
X[42]	X[42]	X	X	H	H	High-Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0–I/O_7); High-Z (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	L	H	High Z (I/O_0–I/O_7); Data Out (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0–I/O_7); High-Z (I/O_8–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	L	H	High-Z (I/O_0–I/O_7); Data In (I/O_8–I/O_{15})	Write	Active (I_{CC})
L	H	H	L	X	X	Data Out (I/O_0–I/O_7)	Read	Active (I_{CC})
L	H	H	H	X	X	High-Z	Output disabled	Active (I_{CC})
L	H	L	X	X	X	Data In (I/O_0–I/O_7)	Write	Active (I_{CC})

Note
42. The ‘X’ (Don’t care) state for the chip enables refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

Ordering Information

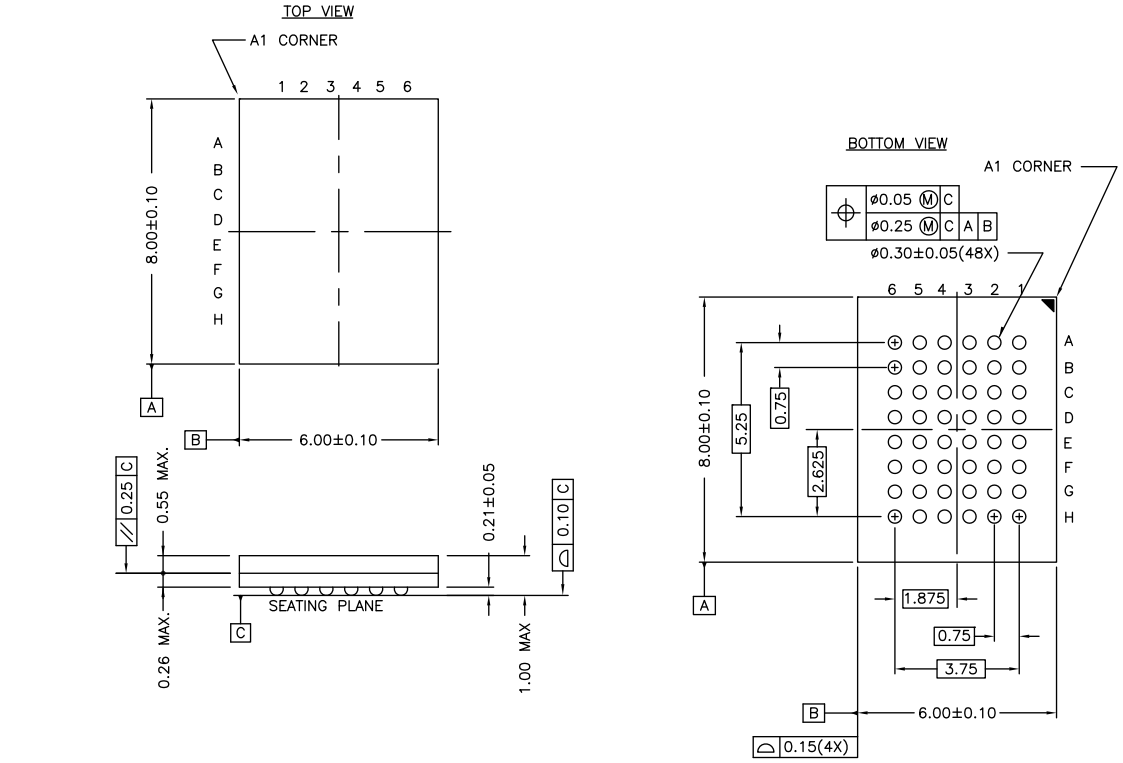
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62157H30-45BVXI	51-85150	48-ball VFBGA (6 × 8 × 1 mm) (Pb-free), Package Code: BZ48	Industrial
	CY62157H30-45BVXIT			

Ordering Code Definitions



Package Diagrams

Figure 11. 48-ball VFBGA (6 × 8 × 1.0 mm) Package Outline, 51-85150

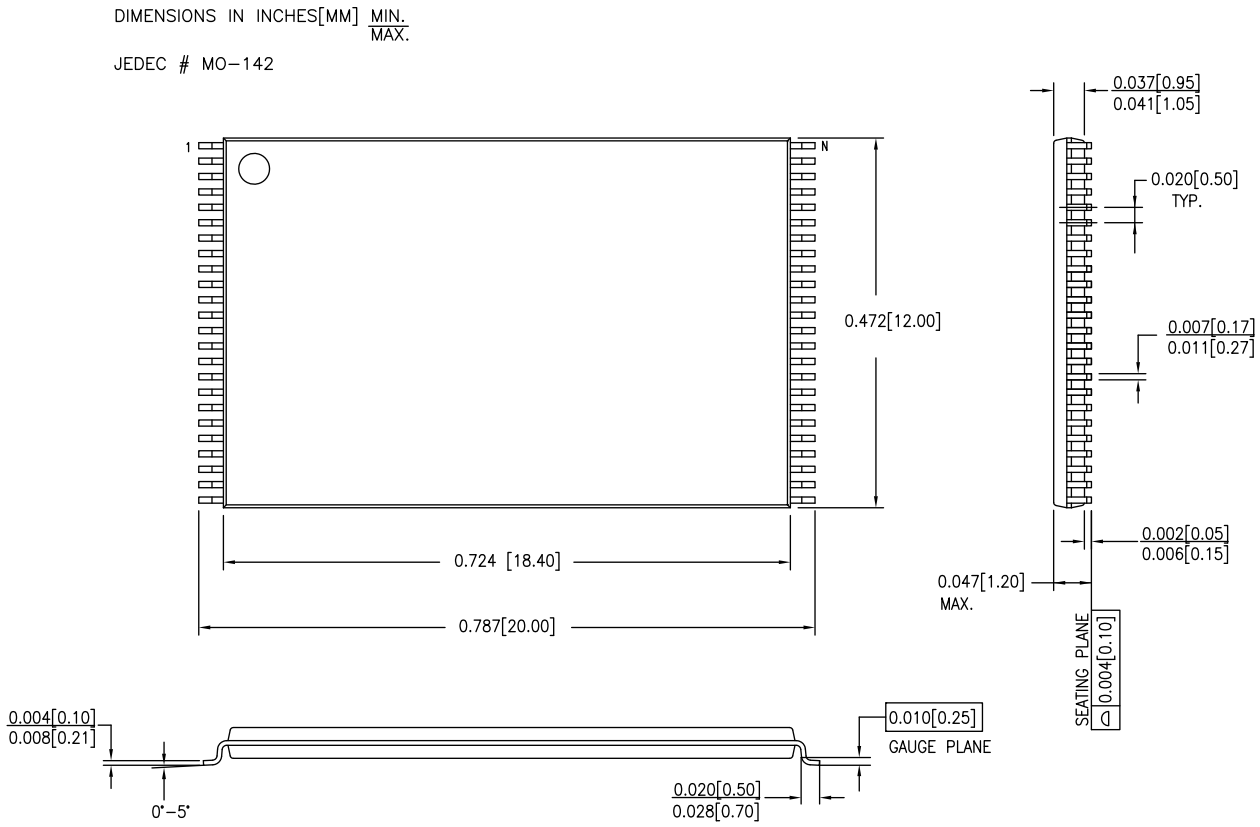


NOTE:
PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.

51-85150 *H

Package Diagrams (continued)

Figure 12. 48-pin TSOP I (12 × 18.4 × 1.0 mm) Package Outline, 51-85183



Acronyms

Acronym	Description
$\overline{BHE}$	byte high enable
$\overline{BLE}$	byte low enable
$\overline{CE}$	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
$\overline{OE}$	output enable
SRAM	static random access memory
VFBGA	very fine-pitch ball grid array
$\overline{WE}$	write enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	Degrees Celsius
MHz	megahertz
µA	microamperes
µs	microseconds
mA	milliamperes
mm	millimeters
ns	nanoseconds
Ω	ohms
%	percent
pF	picofarads
V	volts
W	watts

Document History Page

Document Title: CY62157H MoBL®, 8-Mbit (512K words × 16 bit) Static RAM with Error Correcting Code (ECC) Document Number: 001-88316				
Rev.	**ECN No.**	**Orig. of Change**	**Submission Date**	**Description of Change**
*B	4983842	NILE	10/23/2015	Changed status from Preliminary to Final.
*C	5109716	NILE	01/27/2016	Updated DC Electrical Characteristics: Changed minimum value of V_{OH} parameter from 2.2 V to 2.4 V corresponding to V_{CC} Operating Range “2.7 V to 3.6 V” and Test Condition “V_{CC} = Min, I_{OH} = –1.0 mA”.
*D	5427485	VINI	09/06/2016	Updated Maximum Ratings: Updated Note 4 (Replaced “2 ns” with “20 ns”). Updated DC Electrical Characteristics: Changed minimum value of V_{IH} parameter from 2.0 V to 1.8 V corresponding to the Operating Range “2.2 V to 2.7 V”. Updated Ordering Information: Updated part numbers. Updated to new template. Completing Sunset Review.

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